

Amendments to the Claims:

Claims 1-14 (Cancelled).

15. (New) A contact hole formation method comprising:

forming a first group of gate electrodes on a first region of a substrate so that the first group of gate electrodes are densely arranged;

forming a second group of gate electrodes on a second region of the substrate so that the second group of gate electrodes are sparsely arranged;

depositing a first dielectric film on the first region and the second region of the substrate on which the gate electrodes are formed;

planarizing the first dielectric film;

depositing a second dielectric film on the planarized first dielectric film, the second dielectric film having an etching rate different from an etching rate of the first dielectric film; and

forming contact holes through the first dielectric film and the second dielectric film.

16. (New) The contact hole formation method of claim 15, further comprising planarizing the second dielectric film.

17. (New) The contact hole formation method of claim 15, wherein the first dielectric film is a BPSG film.

18. (New) The contact hole formation method of claim 17, wherein, after said planarization of the first dielectric film, the second dielectric film is deposited on the first dielectric film before a precipitate is formed on a surface of the first dielectric film.

19. (New) The contact hole formation method of claim 18, wherein said depositing of the second dielectric film on the first dielectric film is performed within 24 hours after said planarizing of the first dielectric film.

20. (New) The contact hole formation method of claim 15, further comprising eliminating a precipitate on a surface of the first dielectric film after said planarizing of the first dielectric film.

21. (New) The contact hole formation method of claim 20, wherein said eliminating of the precipitate on the surface of the first dielectric film comprises eliminating the precipitate using a solution.

22. (New) The contact hole formation method of claim 15, wherein the contact holes are formed so as to reach the substrate.

23. (New) The contact hole formation method of claim 15, wherein the contact holes are formed so as to reach the gate electrodes formed on the substrate.

24. (New) The contact hole formation method of claim 15, wherein a distance between at least two adjacent gate electrodes formed on the first region is no greater than $0.3\ \mu\text{m}$.

25. (New) The contact hole formation method of claim 15, wherein the first dielectric film includes substantially 5.0 wt% of phosphorus.

26. (New) The contact hole formation method of claim 15, further comprising heating the first dielectric film before said planarizing of the first dielectric film and after said depositing of the first dielectric film.

27. (New) A contact hole formation method comprising:
forming a first group of interconnections on a first region of a substrate so that the first group of interconnections are densely arranged;
forming a second group of interconnections on a second region of the substrate so that the second group of interconnections are sparsely arranged;
depositing a first dielectric film on the first region and the second region of the substrate

on which the interconnections are formed;

planarizing the first dielectric film;

depositing a second dielectric film on the planarized first dielectric film, the second dielectric film having an etching rate different from an etching rate of the first dielectric film;
and

forming contact holes through the first dielectric film and the second dielectric film.

28. (New) The contact hole formation method of claim 27, wherein a distance between at least two adjacent interconnections formed on the first region is no greater than $0.3\ \mu\text{m}$.

29. (New) A contact hole formation method comprising:

forming a plurality of interconnections on a substrate, the interconnections including a first interconnection and a second interconnection, the first interconnection having a width different than a width of the second interconnection;

depositing a first dielectric film on the substrate on which the interconnections are formed;

planarizing the first dielectric film;

depositing a second dielectric film on the planarized first dielectric film, the second dielectric film having an etching rate different from an etching rate of the first dielectric film;
and

forming contact holes through the first dielectric film and the second dielectric film.

30. (New) The contact hole formation method of claim 29, wherein the first dielectric film includes substantially 5.0 wt% of phosphorus, and the second dielectric film is a non-doped oxide film.

31. (New) The contact hole formation method of claim 29, further comprising heating the first dielectric film before said planarizing of the first dielectric film and after said depositing of the first dielectric film.

32. (New) A contact hole formation method comprising:
forming a first group of gate electrodes on a first region of a substrate so that the first group of gate electrodes are densely arranged;
forming a second group of gate electrodes on a second region of the substrate so that the second group of gate electrodes are sparsely arranged;
depositing a first dielectric film on the first region and the second region of the substrate on which the gate electrodes are formed, the first dielectric film including phosphorus;
heating the first dielectric film;
planarizing the first dielectric film after said heating of the first dielectric film;
depositing a second dielectric film on the planarized first dielectric film, the second dielectric film comprising a non-doped oxide film; and
forming contact holes through the first dielectric film and the second dielectric film

33. (New) The contact hole formation method of claim 32, wherein a distance between at least two adjacent gate electrodes formed on the first region is no greater than $0.3\ \mu\text{m}$.

34. (New) The contact hole formation method of claim 32, further comprising eliminating a precipitate on a surface of the first dielectric film after said planarizing of the first dielectric film and before said depositing of the second dielectric film.